Subsi	iitute for form 144	19/PTO		Application Number 10/608,287			
				Filing Date	June 27, 2003	_	
	DRMATION			First Named Inventor	Yeo, et al.		
(use as many sheets as necessary)				Art Unit	2812		
				Examiner Name	TBD		
Sheet	1	of	2	Attorney Docket Number	TSM03-0421	_	

			U.S. PATE	NT DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number  Number - Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Retevant Passages or Relevant Figures Appear
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Examiner Cite No.1		Foreign Patent Document	0.45.45.4.04.4	Name of Patentee or	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Т		
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Applicant of Cited Document		T*		
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Substitute for form 1449B/PTO		Compl te if Known			
		Application Number	10/608,287		
18.	IEODMATIOI	א שופכו (	SURF	Filing Date	June 27, 2003
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				First Named Inventor	Yeo, et al.
				Group Art Unit	2812
				Examiner Name	TBD
Sheet	2	of	2	Attorney Docket Number	TSM03-0421

		OTHER ROLLS ART. MON BATTAT LITERATURE ROCUMENTS	
		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite,	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue	₹2
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1 Signature   Chandra Chaudharl   Considered   Considered	Examiner Signature	Chandra	Chaudhari	Date Considered	I () (() 1	ı

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